

## P-Channel Enhancement Mode Power MOSFET

### Description

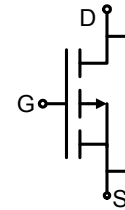
The HM2305B uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

### General Features

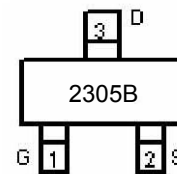
- $V_{DS} = -12V, I_D = -4.1A$   
 $R_{DS(ON)} < 78m\Omega @ V_{GS} = -2.5V$   
 $R_{DS(ON)} < 55m\Omega @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

### Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2305B	HM2305B	SOT-23	Ø180mm	8 mm	3000 units

## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	-12	V
Gate-Source Voltage		$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	$I_D$	-4.1	A
	$T_C = 70^\circ\text{C}$		-3.2	
	$T_A = 25^\circ\text{C}$		-3	
	$T_A = 70^\circ\text{C}$		-2.3	
Drain Current -Pulsed (Note 1)		$I_{DM}$	-15	A
Maximum Power Dissipation		$P_D$	1.7	W
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 To 150	$^\circ\text{C}$

## Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	74	$^\circ\text{C/W}$
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**Electrical Characteristics ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-12	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-0.4	-0.7	-1.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.1A	-	40	55	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-3A	-	55	78	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V,I <sub>D</sub> =-2A	6	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-4V,V <sub>GS</sub> =0V, F=1.0MHz	-	740	-	PF
Output Capacitance	C <sub>oss</sub>		-	290	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	190	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-4V,I <sub>D</sub> =-3.3A , R <sub>L</sub> =-1.2Ω,V <sub>GEN</sub> =-4.5V,R <sub>g</sub> =1Ω	-	12	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	35	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	30	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-4V,I <sub>D</sub> =-4.1A,V <sub>GS</sub> =-4.5V	-	7.8	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.2	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-1.6A	-	-	-1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	1.6	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

# Typical Electrical and Thermal Characteristics

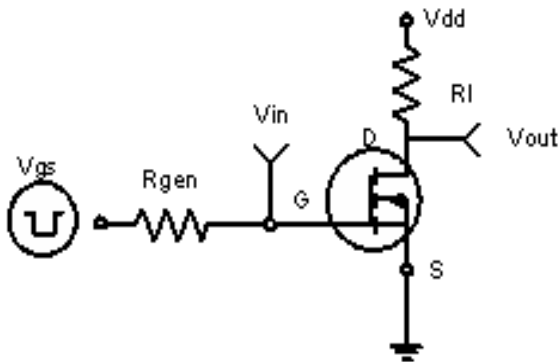


Figure 1: Switching Test Circuit

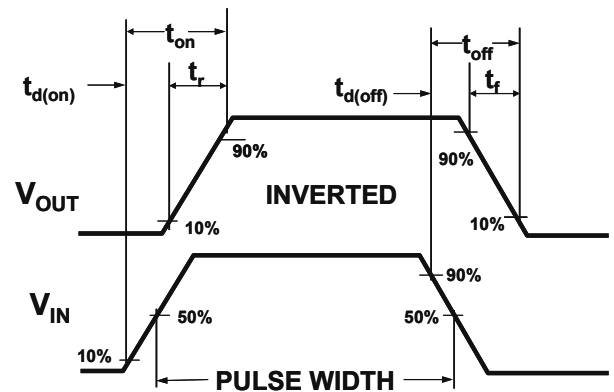


Figure 2: Switching Waveforms

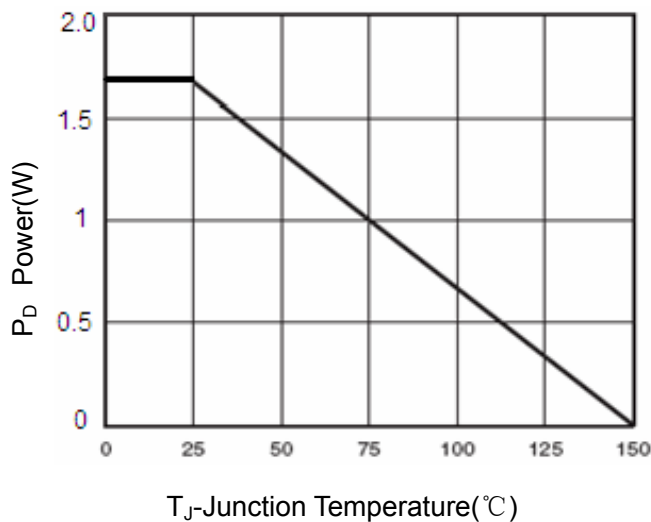


Figure 3 Power Dissipation

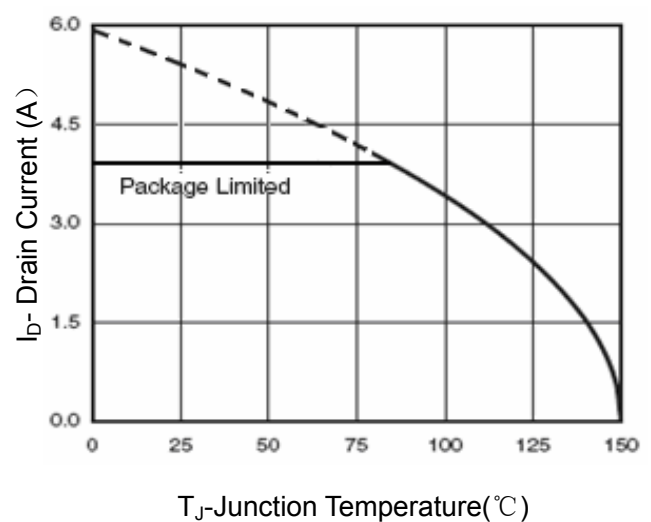


Figure 4 Drain Current

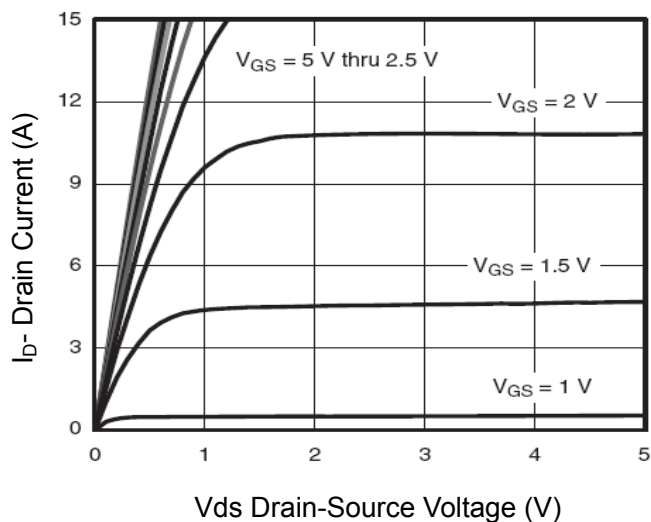


Figure 5 Output Characteristics

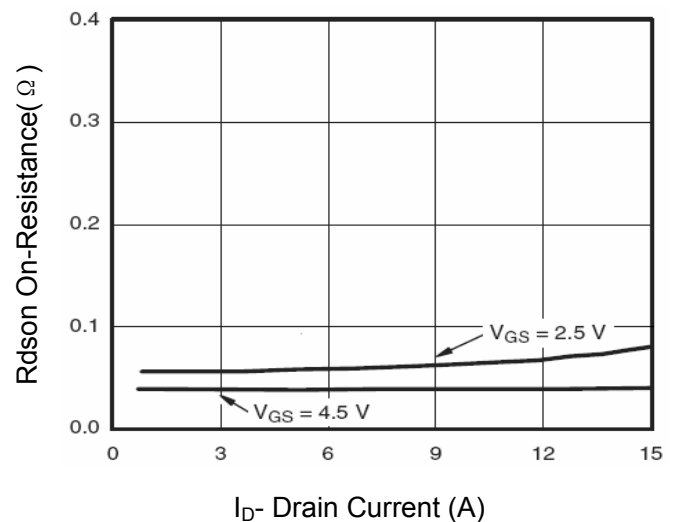
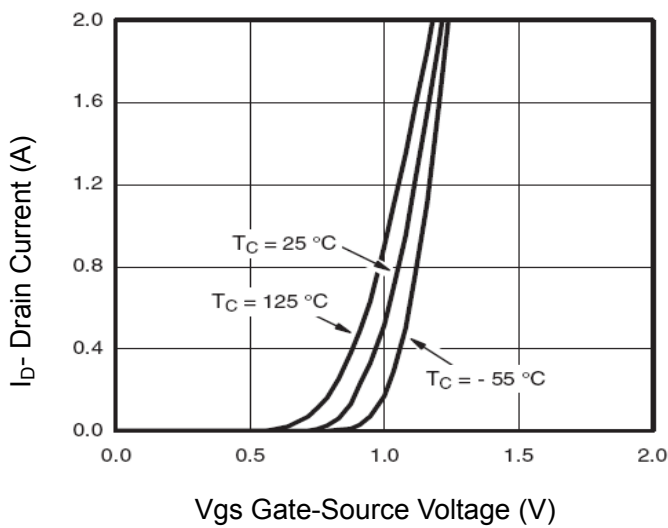
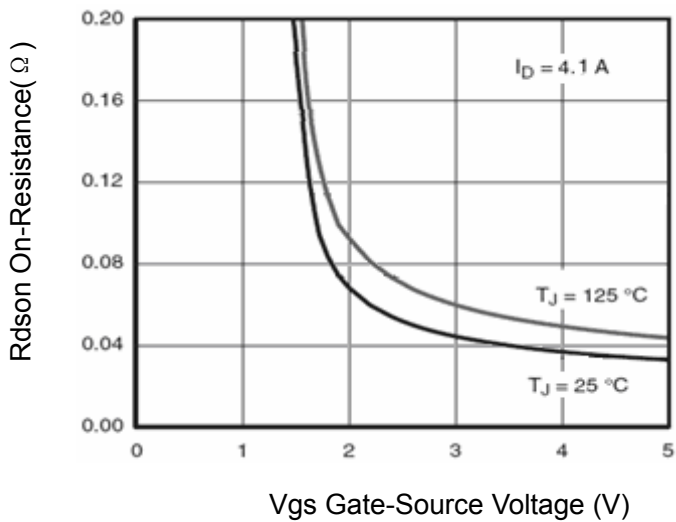


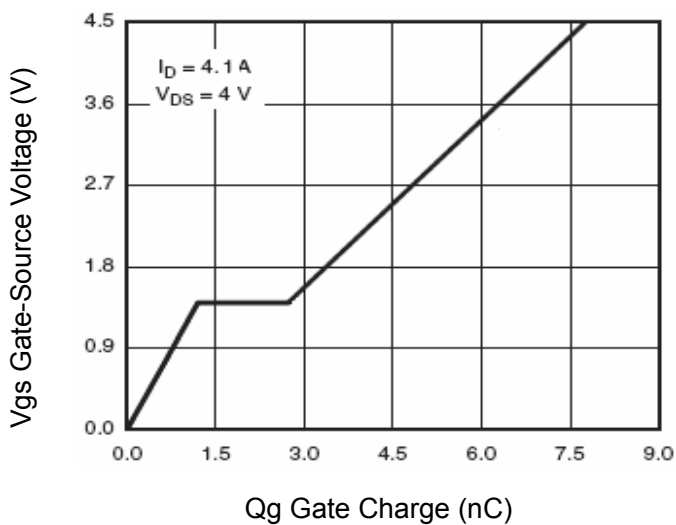
Figure 6 Drain-Source On-Resistance



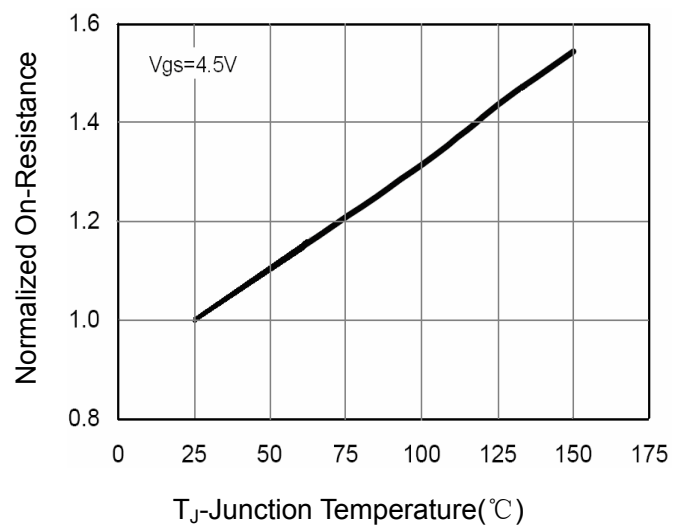
**Figure 7 Transfer Characteristics**



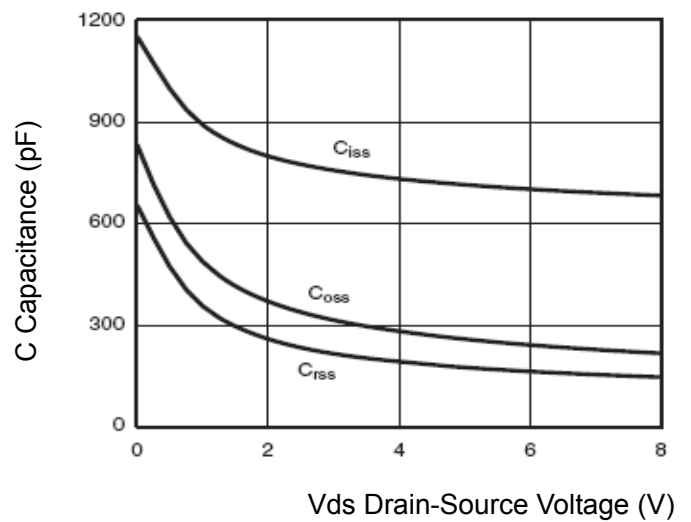
**Figure 9 Rdson vs Vgs**



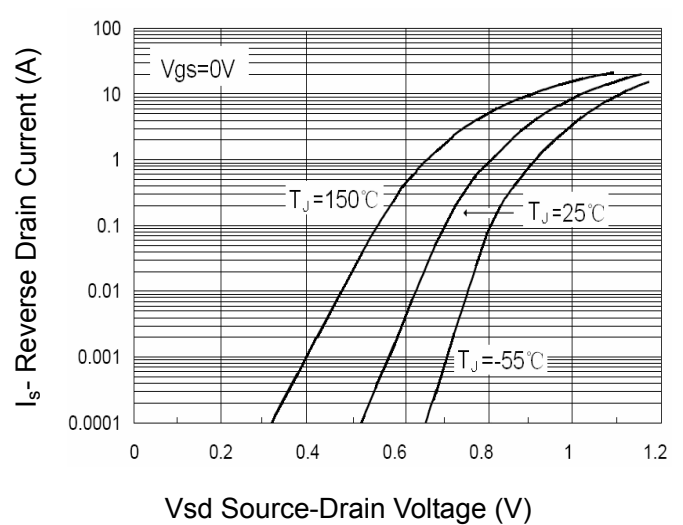
**Figure 11 Gate Charge**



**Figure 8 Drain-Source On-Resistance**



**Figure 10 Capacitance vs Vds**



**Figure 12 Source- Drain Diode Forward**

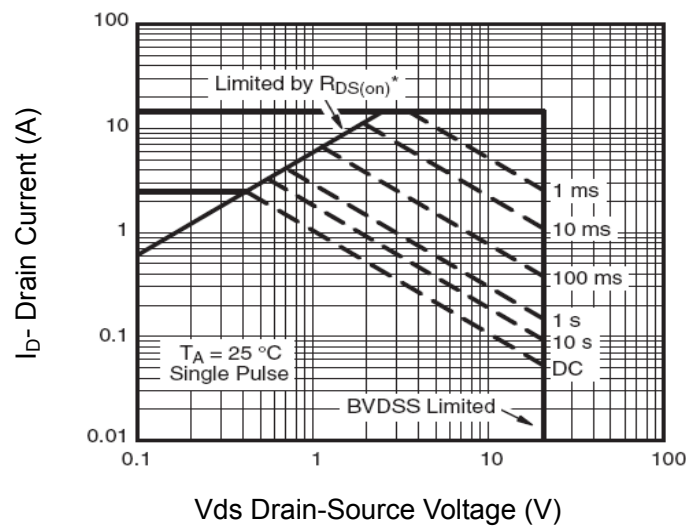


Figure 13 Safe Operation Area

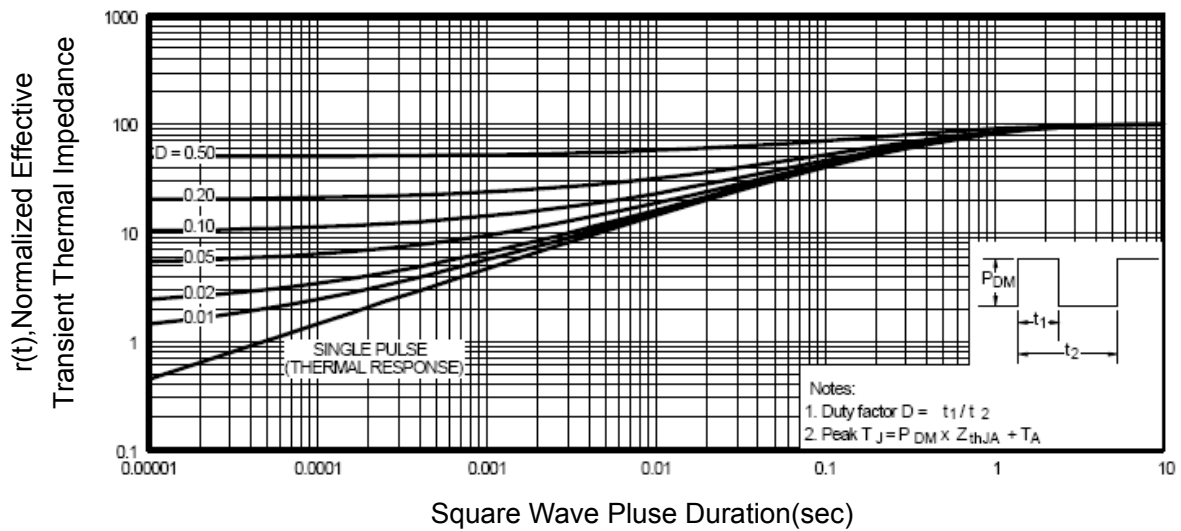
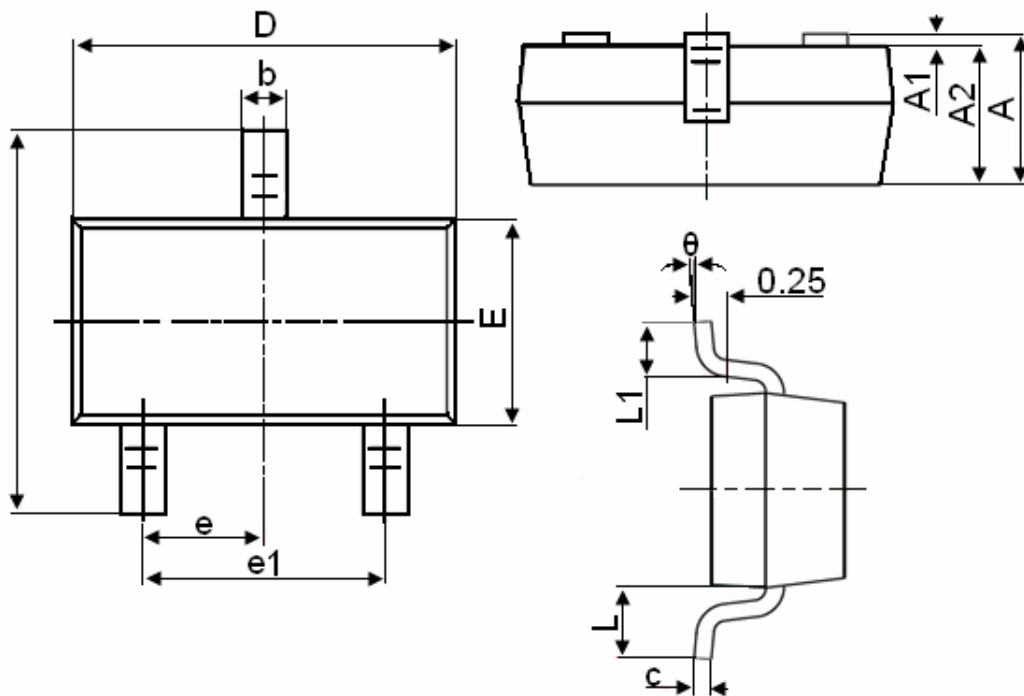


Figure 14 Normalized Maximum Transient Thermal Impedance

## SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

## Notes

1. All dimensions are in millimeters.
2. Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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